

WE CLAIM:

sub A2
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1. A method for forming a spacer, comprising:
depositing an oxide layer over a polysilicon line of a core and periphery

area;

performing a first spacer in the core and periphery area;
implanting an area located between polysilicon lines in the core area;
applying a second oxide layer over the core and periphery areas; and
performing a second spacer etch over the periphery area wherein
a difference appearance of the core and periphery areas is produced.

2. The method of claim 1 wherein the first oxide deposition has
a thickness of less than one-half the distance between a periphery of the
polysilicon lines.

3. A non volatile memory device made by the method of claim 1.
4. A non volatile memory device made by the method of claim 2.
- add A3*